

Serial N . 09/633,857
Art Unit: 1765

REMARKS

Applicant made self-explanatory amendments to independent claims 1 and 11.

35 USC 103

To the extent any art rejection continues to be applied against claims 1, 11 (as amended), reconsideration is respectfully requested.

Applicant believes neither Nishizawa, Maley, Abelson nor Dubbelday, whether applied either singly or in combination, teaches, discloses or suggests "introducing at least two gases according substantially to the gas flow profiles depicted in regions I, II, V and VI of Figure 4" (amended claims 1, 11).

Thus, Applicant believes any rejection is overcome, without the introduction of new matter. See also, for example, page 12, lines 10-20, of the application as filed.

Accordingly, entry of this Amendment, reconsideration and allowance of claims 1-20 are solicited.

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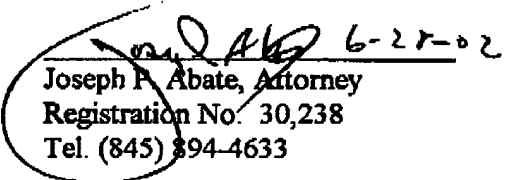
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Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. **This appendix is captioned "Version with Markings to Show Changes Made".**

Respectfully submitted,
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Attachment: Appendix - Version with Markings to Show Changes Made

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

Claims 1 and 11 have been amended as follows:

1. (Amended) A method of depositing a film containing silicon on a crystalline silicon surface, said method including steps of
introducing a gas containing precursor material into a reaction vessel,
adsorbing an activated species formed from said precursor material on said crystalline silicon surface, and
determining a partial pressure of hydrogen in residual gases as said activated species is deposited on said crystalline silicon surface,
wherein said step of introducing includes introducing at least two gases according substantially to gas flow profiles depicted in regions I, II, V and VI of Figure 4.
11. (Amended) Apparatus for depositing a film containing silicon on a crystalline silicon surface including
means for introducing a gas containing precursor material into a reaction vessel such that an activated species formed from said precursor material is adsorbed on said crystalline silicon surface, and
means for determining a partial pressure of hydrogen in residual gases as said activated species is deposited on said crystalline silicon surface,

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wherein said means for introducing includes means for introducing at least two gases according substantially to gas flow profiles depicted in regions I, II, V and VI of Figure 4.

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